L Number	Hits	Search 1	DB	Time stamp
1	896	laser n: ((alignment align\$3) adj mark)	USPAT;	2002/11/07 11:19
		*# (US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
8	2	(laser near15 ((alignment align\$3) adj mark)) same ((alpha or	USPAT;	2002/11/07 11:22
		amorphous or a) adj silicon)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
[IBM_TDB	
15	21	(laser near15 ((alignment align\$3) adj mark)) and ((alpha or	USPAT;	2002/11/07 11:23
1		amorphous or a) adj silicon)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
22	47562	TFT (thin adj film adj (transistor device))	USPAT;	2002/11/07 11:40
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
29	4014	(deposit\$3 form\$3 anneal\$3 heat\$3 oxidis\$3 oxidiz\$3)	USPAT;	2002/11/07 11:47
1		near10 (dielectric insulation oxide dioxide SiO2 "SiO.sub.2"	US-PGPUB;	
		SiO) near10 (protect\$3 prevent\$3) near10 etch\$3	EPO; JPO;	
			DERWENT;	
		. <u></u> ,	IBM_TDB	
36	202	(TFT (thin adj film adj (transistor device))) and ((deposit\$3	USPAT;	2002/11/07 11:46
		form\$3 anneal\$3 heat\$3 oxidis\$3 oxidiz\$3) near10 (dielectric	US-PGPUB;	
		insulation oxide dioxide SiO2 "SiO.sub.2" SiO) near10	EPO; JPO;	
		(protect\$3 prevent\$3) near10 etch\$3)	DERWENT;	
1.0		/// 1/40 / 40 / 40 / 40 / 40 / 40 / 40 /	IBM_TDB	
43	1763	((deposit\$3 form\$3 anneal\$3 heat\$3 oxidis\$3 oxidiz\$3)	USPAT;	2002/11/07 11:48
	į	near10 (dielectric insulation oxide dioxide SiO2 "SiO.sub.2"	US-PGPUB;	
	,	SiO) near10 (protect\$3 prevent\$3) near10 etch\$3) near15 (si	EPO; JPO;	
	,	silicon semiconductor)	DERWENT;	
50	400	/TET //bin a di film a di //manadatan da da AMA (1/4)	IBM_TDB	0000444074446
50	108	(TFT (thin adj film adj (transistor device))) and (((deposit\$3	USPAT;	2002/11/07 11:48
		form\$3 anneal\$3 heat\$3 oxidis\$3 oxidiz\$3) near10 (dielectric	US-PGPUB;	
		insulation oxide dioxide SiO2 "SiO.sub.2" SiO) near10	EPO; JPO;	
		(protect\$3 prevent\$3) near10 etch\$3) near15 (si silicon	DERWENT;	
		semiconductor))	IBM_TDB	